ME70N03S/ME70N03S-G

30V N-Channel Enhancement Mode MOSFET

GENERAL DESCRIPTION

The ME70N03S is the N-Channel logic enhancement mode power field effect transistors are produced using high cell density, DMOS trench technology. This high density process is especially tailored to minimize on-state resistance. These devices are particularly suited for low voltage application such as cellular phone and notebook computer power management and other battery powered circuits where high-side switching and low in-line power loss are needed in a very small outline surface mount package.

FEATURES

- $R_{DS(ON)} \leqq 6.6m\Omega @ V_{GS}=10V$
- $R_{DS(ON)} \leqq 11m\Omega @ V_{GS}=4.5V$
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability

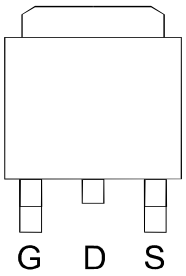
APPLICATIONS

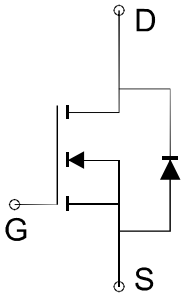
- Power Management in Note book
- Portable Equipment
- Battery Powered System
- DC/DC Converter
- Load Switch
- DSC

PIN CONFIGURATION

(TO-252)

Top View





Ordering Information:ME70N03S (Pb-free)

ME70N03S-G (Green product-Halogen free)

Absolute Maximum Ratings (T_A=25℃ Unless Otherwise Noted)

Parameter		Symbol	Maximum Ratings	Unit
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current*	T_C=25℃	I_D	62	A
	T_C=70℃		50	
	T_A=25℃		17	
	T_A=70℃		13	
Pulsed Drain Current		I_{DM}	248	A
Maximum Power Dissipation	T_C=25℃	P_D	41	W
	T_C=70℃		26	
	T_A=25℃		3.1	
	T_A=70℃		2	
Operating Junction and Storage Temperature Range		T_J, Tstg	-55 to 150	℃
Thermal Resistance-Junction to Case		$R_{\theta JC}$	3	℃/W

*The device mounted on 1in^2 FR4 board with 2 oz copper

30V N-Channel Enhancement Mode MOSFET

Electrical Characteristics (T_A=25℃ Unless Otherwise Specified)

Symbol	Parameter	Limit	Min	Typ	Max	Unit
STATIC						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250μA	30			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250μA	1		3	V
I_{GSS}	Gate-Body Leakage	V_{DS}=0V, V_{GS}=±20V			±100	nA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=30V, V_{GS}=0V			1	μA
$R_{DS(ON)}$	Drain-Source On-State Resistance[a]	V_{GS}=10V, I_D=30A		5.5	6.6	mΩ
		V_{GS}=4.5V, I_D=15A		8.5	11	
V_{SD}	Diode Forward Voltage	I_S=20A, V_{GS}=0V		0.85	1.2	V
DYNAMIC						
Qg	Total Gate Charge	V_{DS}=15V, V_{GS}=10V, I_D=25A		38		nC
Qg	Total Gate Charge	V_{DS}=15V, V_{GS}=4.5V, I_D=25A		19.5		
Qgs	Gate-Source Charge			8		
Qgd	Gate-Drain Charge			11		
Ciss	Input Capacitance	V_{DS}=15V, V_{GS}=0V, F=1MHz		1620		pF
Coss	Output Capacitance			255		
Crss	Reverse Transfer Capacitance			80		
Rg	Gate Resistance	V_{DS}=0V, V_{GS}=0V, f=1MHz		1.1		Ω
$t_{d(on)}$	Turn-On Delay Time	R_L=15Ω, V_{GEN}=10V, I_D=1A V_{DD}=15V, R_G=3Ω		17		ns
tr	Turn-On Rise Time			15		
$t_{d(off)}$	Turn-Off Delay Time			58		
tf	Turn-Off Fall Time			6		

Note: a.Pulse test: pulse width＜=300us, duty cycle＜=2%

b. Matsuki Electric/ Force mos reserves the right to improve product design, functions and reliability without notice.

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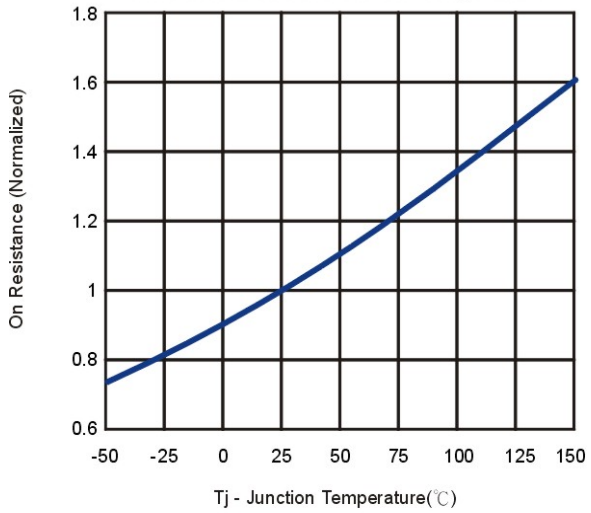
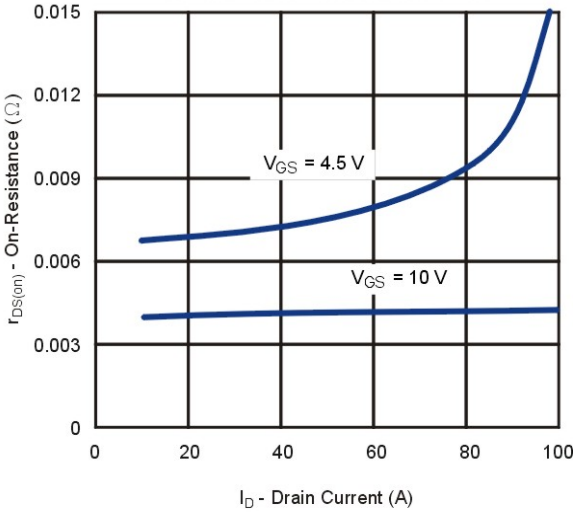
Typical Characteristics (T_J =25℃ Noted)

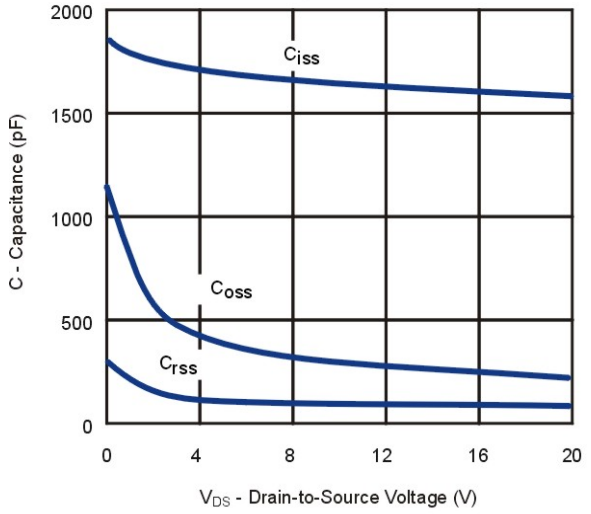
On Resistance vs. Junction Temperature



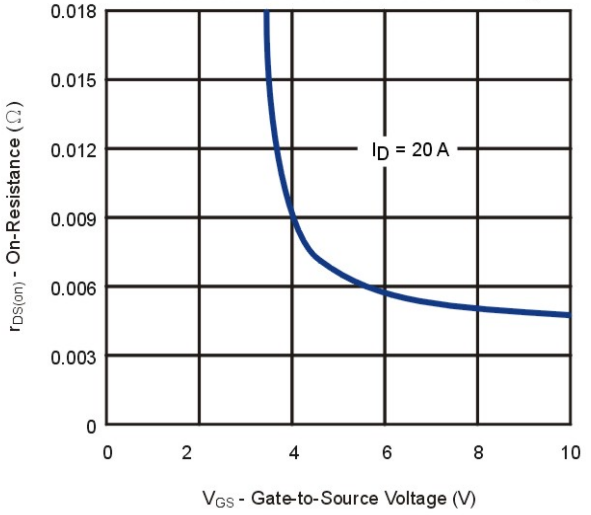
On-Resistance vs. Drain Current



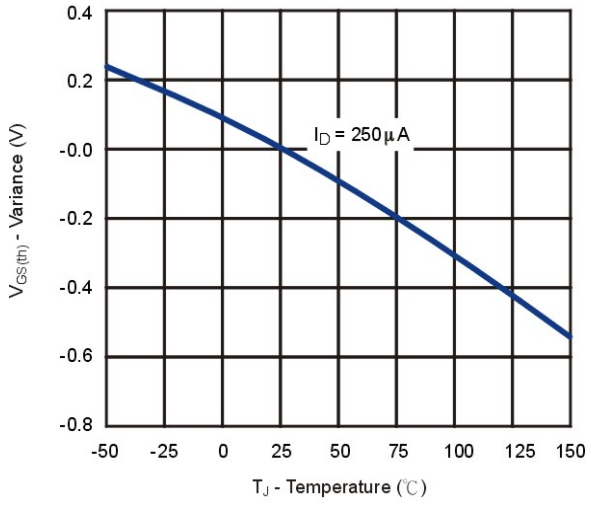
Capacitance



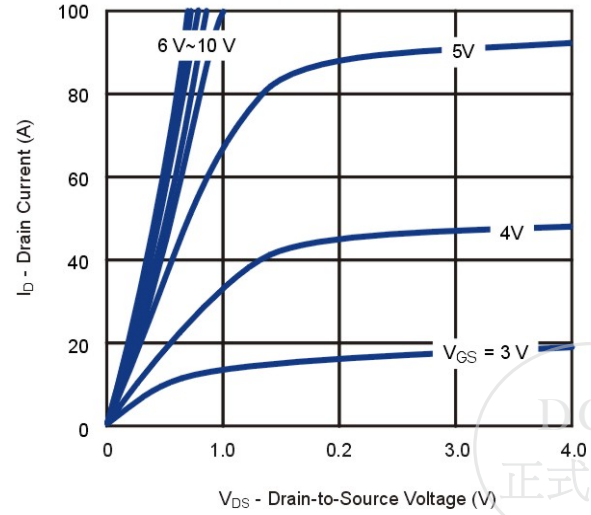
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



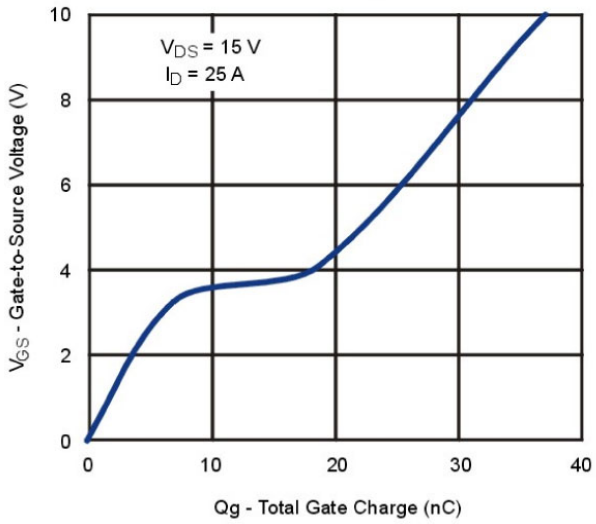
On-Region Characteristics



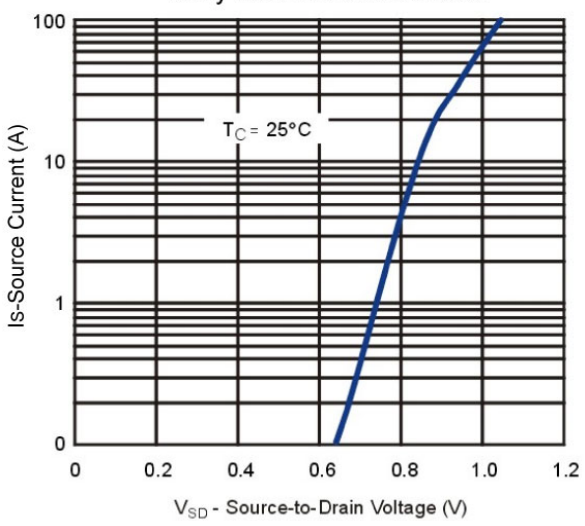
30V N-Channel Enhancement Mode MOSFET

Typical Characteristics (T_J =25℃ Noted)

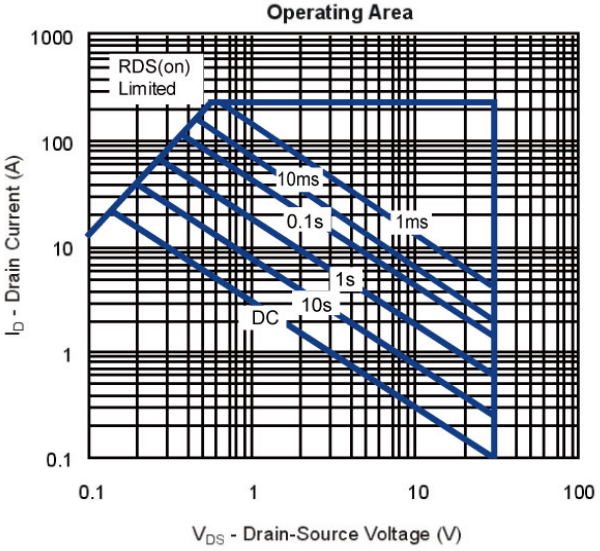
Gate Charge



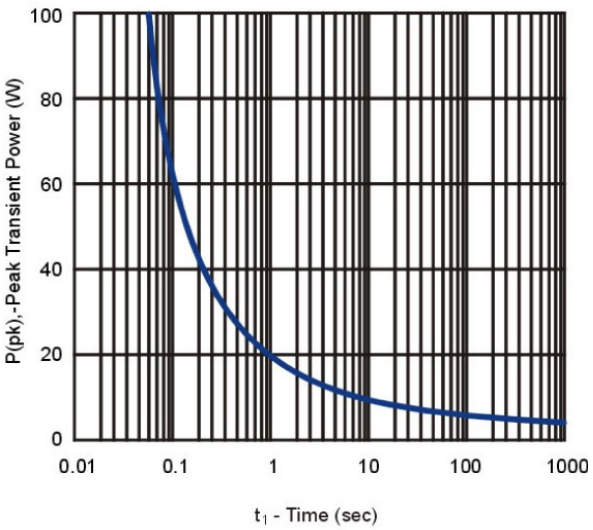
Body-diode characteristics



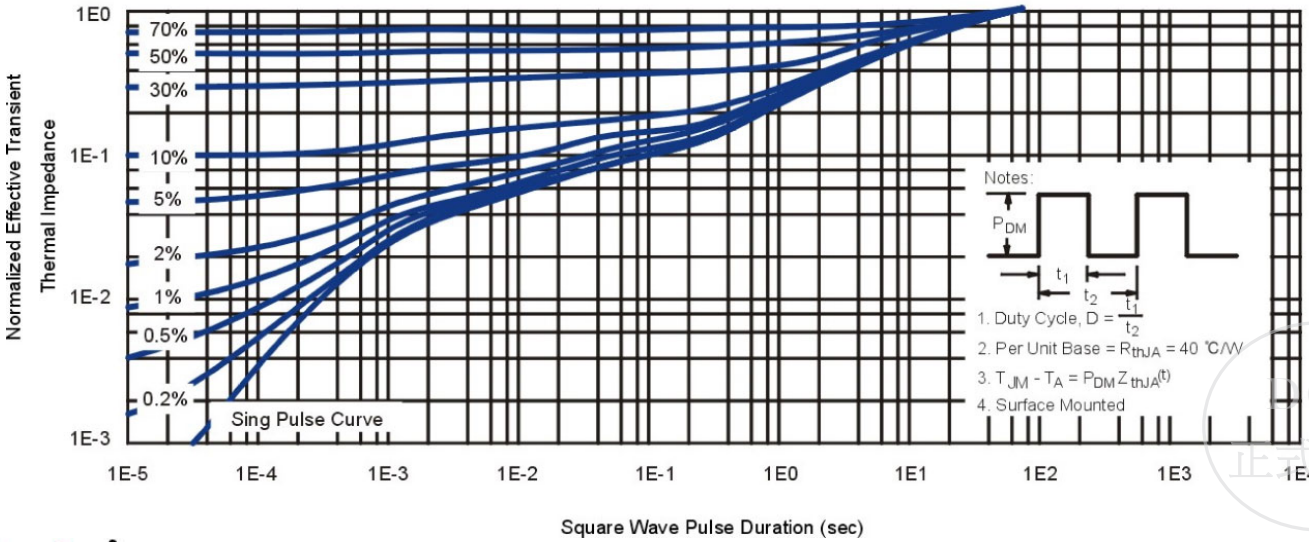
Maximum Forward Biased Safe Operating Area



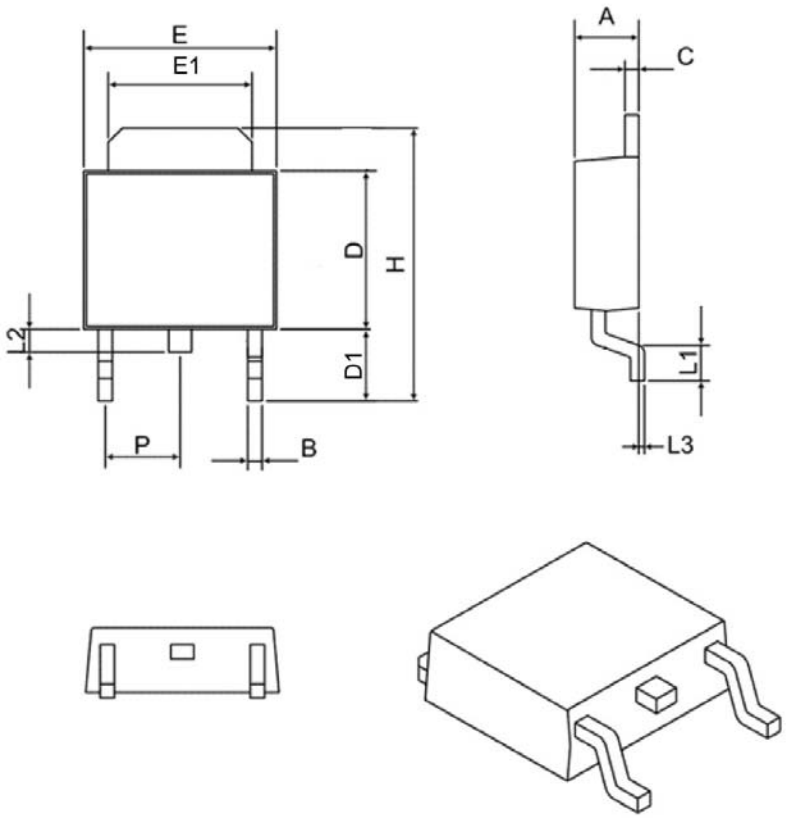
Single Pulse Maximum Power Dissipation



Normalized Thermal Transient Impedance, Junction-to-Ambient



TO-252 Package Outline



SYMBOL	MIN	MAX
A	2.10	2.50
B	0.40	0.90
C	0.40	0.90
D	5.30	6.30
D1	2.20	2.90
E	6.30	6.75
E1	4.80	5.50
L1	0.90	1.80
L2	0.50	1.10
L3	0.00	0.20
H	8.90	10.40
P	2.30 BSC	